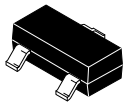
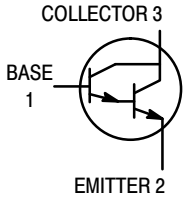
Darlington Transistor

NPN Silicon

MMBT6427LT1G, SMMBT6427LT1G



SOT-23 (TO-236)
CASE 318
STYLE 6



Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	40	Vdc
Collector - Base Voltage	V_{CBO}	40	Vdc
Emitter - Base Voltage	V_{EBO}	12	Vdc
Collector Current – Continuous	I_C	500	mAdc

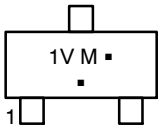
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T_A = 25 °C Derate above 25 °C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25 °C Derate above 25 °C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

MARKING DIAGRAM



1V = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

* Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector - Emitter Breakdown Voltage (I_C = 10 mAdc, V_{BE} = 0)	$V_{(BR)CEO}$	40	–	Vdc
Collector - Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	–	Vdc
Emitter - Base Breakdown Voltage (I_C = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	12	–	Vdc
Collector Cutoff Current (V_{CE} = 25 Vdc, I_B = 0)	I_{CES}	–	1.0	μAdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	–	50	nAdc
Emitter Cutoff Current (V_{EB} = 10 Vdc, I_C = 0)	I_{EBO}	–	50	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) (I_C = 100 mAdc, V_{CE} = 5.0 Vdc) (I_C = 500 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	10,000 20,000 14,000	100,000 200,000 140,000	–
Collector - Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 0.5 mAdc) (I_C = 500 mAdc, I_B = 0.5 mAdc)	$V_{CE(sat)}$ (3)	– –	1.2 1.5	Vdc
Base - Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 0.5 mAdc)	$V_{BE(sat)}$	–	2.0	Vdc
Base - Emitter On Voltage (I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	–	1.75	Vdc
SMALL - SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	7.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	–	15	pF
Current Gain – High Frequency (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	$\|h_{fe}\|$	1.3	–	Vdc
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, R_S = 100 kΩ, f = 1.0 kHz)	NF	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

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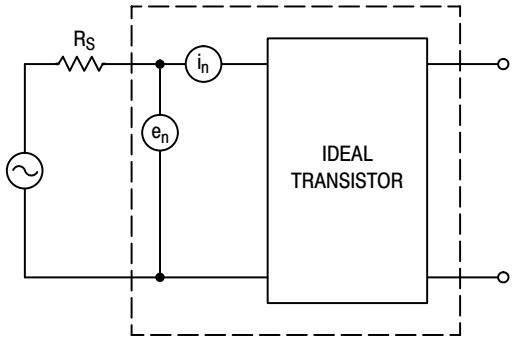


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

(V_{CE} = 5.0 VDC, T_A = 25 °C)

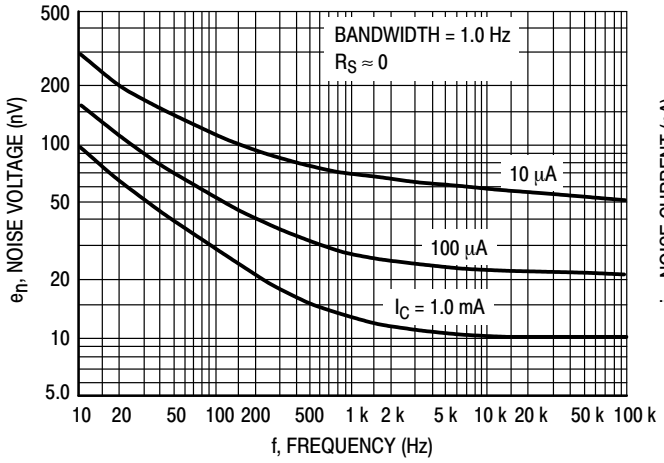


Figure 2. Noise Voltage

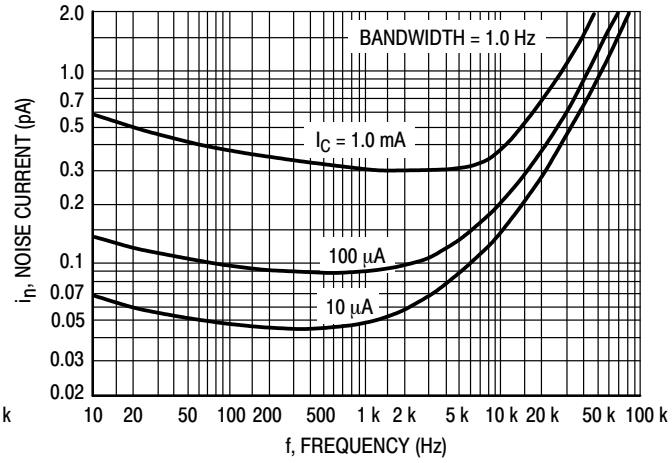


Figure 3. Noise Current

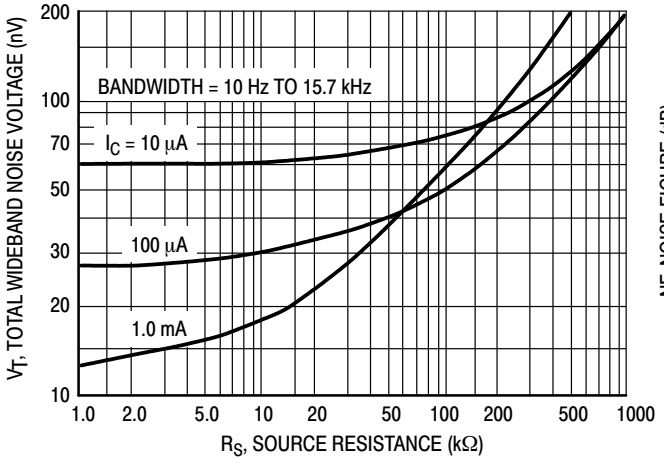


Figure 4. Total Wideband Noise Voltage

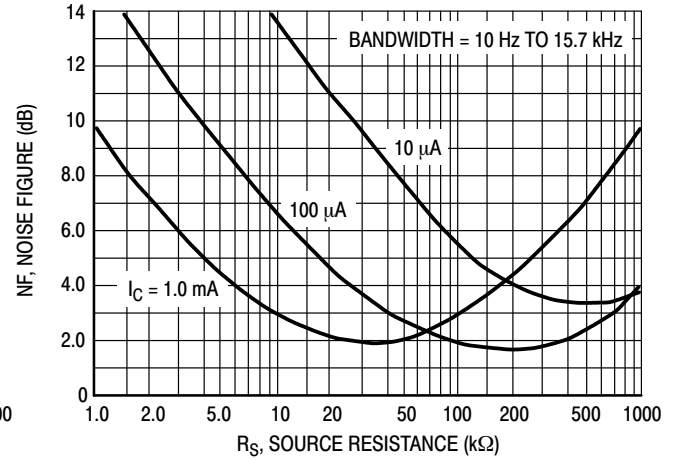


Figure 5. Wideband Noise Figure

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SMALL-SIGNAL CHARACTERISTICS

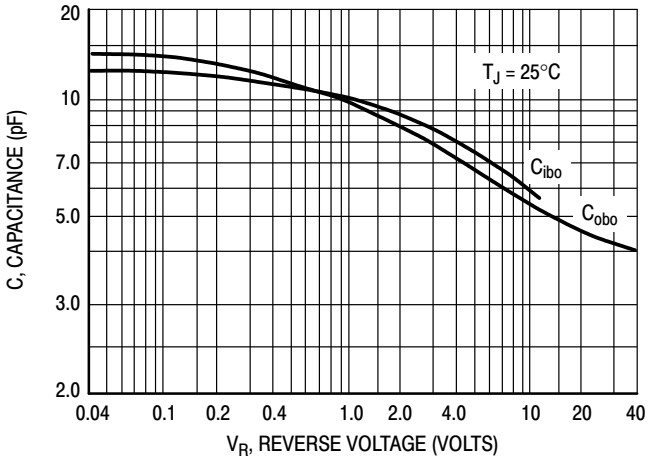


Figure 6. Capacitance

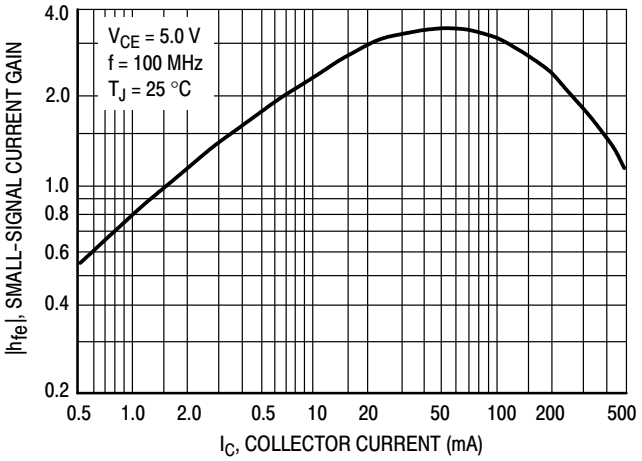


Figure 7. High Frequency Current Gain

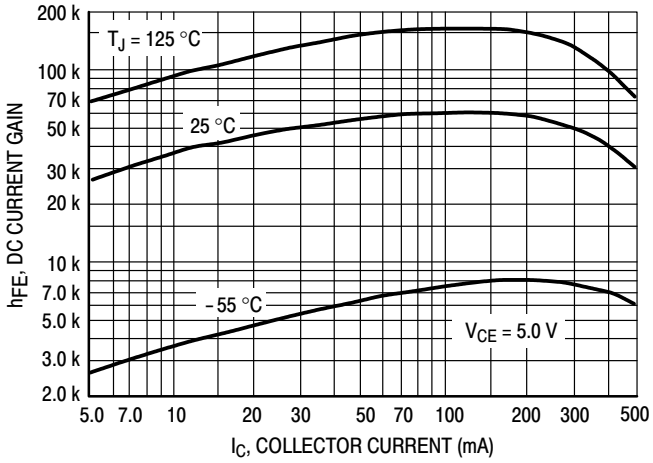


Figure 8. DC Current Gain

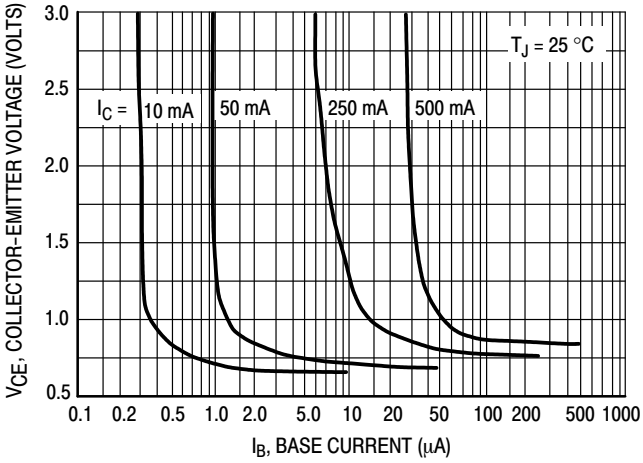


Figure 9. Collector Saturation Region

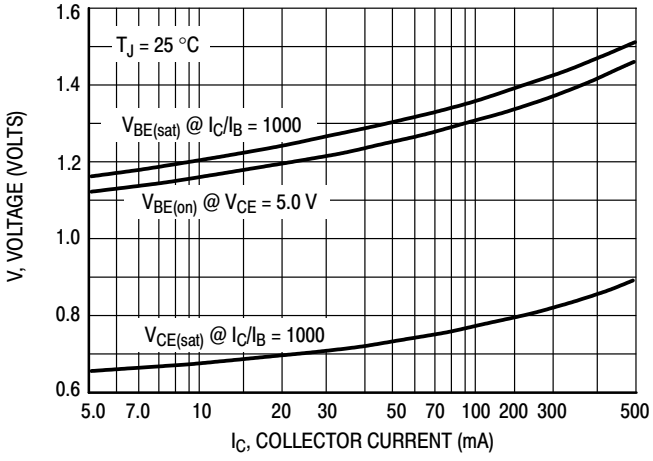


Figure 10. “On” Voltages

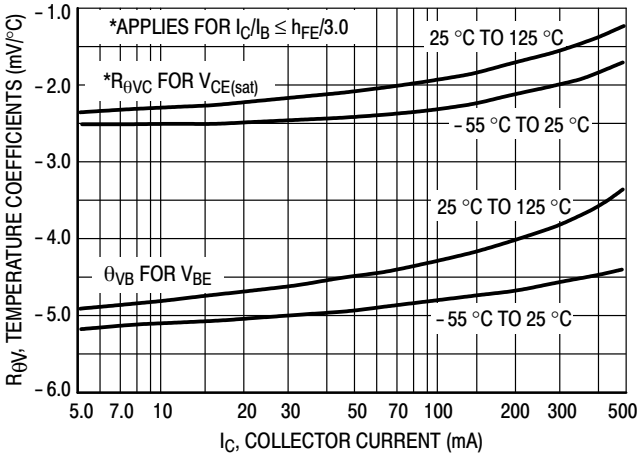


Figure 11. Temperature Coefficients

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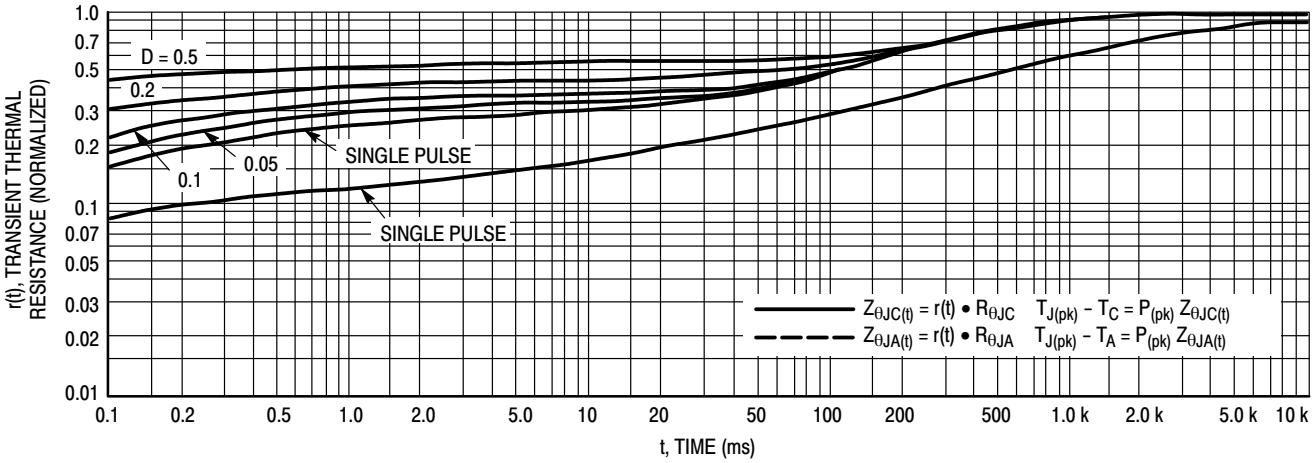
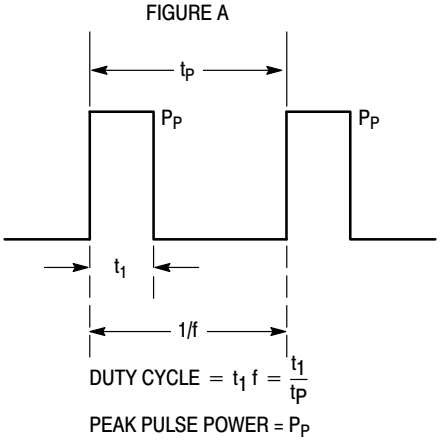


Figure 12. Thermal Response



Design Note: Use of Transient Thermal Resistance Data

ORDERING INFORMATION

Device	Marking	Package	Shipping†
MMBT6427LT1G MMBT6427LT1G-NC SMMBT6427LT1G* SMMBT6427LT1G-NC*	1V	SOT-23 (Pb-Free)	3,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

* S, V and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

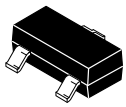
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REVISION HISTORY

Revision	Description of Changes	Date
7	Added OPNs MMBT6427LT1G-NC, SMMBT6427LT1G-NC to Ordering Information table and moved the table from the first page to page 5.	9/23/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

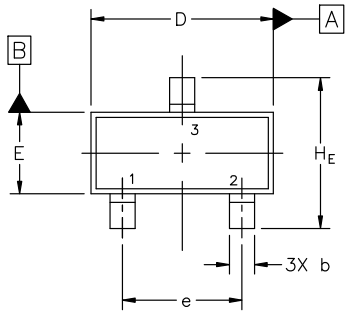
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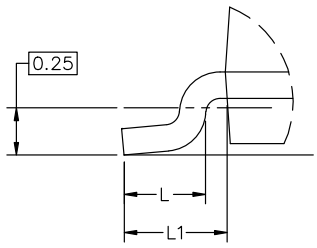
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

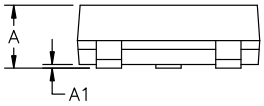
DATE 14 AUG 2024



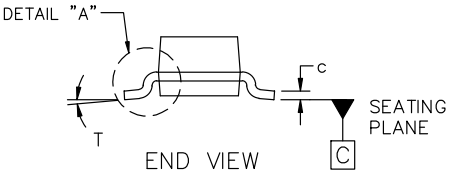
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

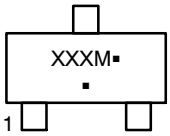


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

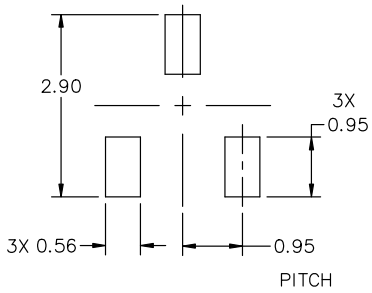
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

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CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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